

Christian Manz

List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

31
papers

544
citations

14
h-index

22
g-index

39
ext. papers

658
ext. citations

2.6
avg, IF

3.1
L-index

#	Paper	IF	Citations
31	Improved AlScN/GaN heterostructures grown by metal-organic chemical vapor deposition. <i>Semiconductor Science and Technology</i> , 2021 , 36, 034003	1.8	14
30	Metalorganic chemical vapor phase deposition of AlScN/GaN heterostructures. <i>Journal of Applied Physics</i> , 2020 , 127, 195704	2.5	17
29	Epitaxial growth of GaN/Ga ₂ O ₃ and Ga ₂ O ₃ /GaN heterostructures for novel high electron mobility transistors. <i>Journal of Crystal Growth</i> , 2020 , 534, 125511	1.6	16
28	Metal-Organic Chemical Vapor Deposition of Aluminum Scandium Nitride. <i>Physica Status Solidi - Rapid Research Letters</i> , 2020 , 14, 1900535	2.5	34
27	Epitaxial growth optimization of AlGaIn/GaN high electron mobility transistor structures on 3C-SiC/Si. <i>Journal of Applied Physics</i> , 2019 , 125, 235701	2.5	7
26	Suppression of Iron Memory Effect in GaN Epitaxial Layers. <i>Physica Status Solidi (B): Basic Research</i> , 2018 , 255, 1700377	1.3	17
25	2- μ m high-brilliance micro-cavity VECSEL with >2W output power 2014 ,		2
24	Micro-cavity 2- μ m GaSb-based semiconductor disk laser using high-reflectivity SiC heatspreader. <i>Applied Physics Letters</i> , 2013 , 103, 041117	3.4	1
23	. <i>IEEE Journal of Quantum Electronics</i> , 2013 , 49, 314-324	2	15
22	. <i>IEEE Journal of Selected Topics in Quantum Electronics</i> , 2013 , 19, 1501908-1501908	3.8	14
21	High-power 2.0 μ m semiconductor disk laser Influence of lateral lasing. <i>Applied Physics Letters</i> , 2012 , 100, 192107	3.4	9
20	Semiconductor disk laser at 2.05 μ m wavelength with . <i>Applied Physics Letters</i> , 2012 , 100, 031109	3.4	16
19	Electro-optically cavity dumped 2 μ m semiconductor disk laser emitting 3 ns pulses of 30 W peak power. <i>Applied Physics Letters</i> , 2012 , 101, 141121	3.4	13
18	Continuous-wave room-temperature operation of a 2.8 μ m GaSb-based semiconductor disk laser. <i>Optics Letters</i> , 2011 , 36, 319-21	3	29
17	2 μ m semiconductor disk laser with a heterodyne linewidth below 10 kHz. <i>Optics Letters</i> , 2011 , 36, 3587-93		12
16	Sub-MHz-Linewidth 200-mW Actively Stabilized 2.3- μ m Semiconductor Disk Laser. <i>IEEE Photonics Technology Letters</i> , 2011 , 23, 1538-1540	2.2	9
15	GaSb-based optically pumped semiconductor disk lasers emitting in the 2.0-2.8 μ m wavelength range 2010 ,		6

14	Investigation of thermal management in optically pumped, antimonide VECSELs. <i>Microelectronics Journal</i> , 2009 , 40, 558-561	1.8	8
13	Quaternary GaInAsSb/AlGaAsSb vertical-external-cavity surface-emitting lasers: A challenge for MBE growth. <i>Journal of Crystal Growth</i> , 2009 , 311, 1920-1922	1.6	6
12	Output power enhancement of 100% for quaternary GaInAsSb/AlGaAsSb semiconductor disc lasers grown with a sequential growth scheme. <i>Journal of Crystal Growth</i> , 2009 , 311, 4158-4161	1.6	3
11	GaSb-Based Optically Pumped Semiconductor Disk Laser Using Multiple Gain Elements. <i>IEEE Photonics Technology Letters</i> , 2009 , 21, 848-850	2.2	10
10	Quantum Cascade Detectors. <i>IEEE Journal of Quantum Electronics</i> , 2009 , 45, 1039-1052	2	141
9	Midinfrared quantum cascade detector with a spectrally broad response. <i>Applied Physics Letters</i> , 2008 , 93, 221106	3.4	42
8	An improved active region concept for highly efficient GaSb-based optically in-well pumped vertical-external-cavity surface-emitting lasers. <i>Applied Physics Letters</i> , 2008 , 93, 181113	3.4	8
7	GaInAs/AlAsSb Quantum Cascade Lasers: A New Approach towards 3-to-5 μm Semiconductor Lasers 2008 , 223-237		
6	Experimental investigation of the lattice and electronic temperatures in Ga _{0.47} In _{0.53} As/Al _{0.62} Ga _{0.38} As _{1-x} Sbx quantum-cascade lasers. <i>Applied Physics Letters</i> , 2007 , 90, 121109	3.4	20
5	High peak-power (10.5W) GaInAs/AlGaAsSb quantum-cascade lasers emitting at $\lambda = 3.6\mu\text{m}$. <i>Applied Physics Letters</i> , 2007 , 90, 121134	3.4	13
4	Resonant optical in-well pumping of an (AlGaIn)(AsSb)-based vertical-external-cavity surface-emitting laser emitting at 2.35 μm . <i>Applied Physics Letters</i> , 2007 , 91, 091113	3.4	24
3	Electronic and thermal properties of Sb-based QCLs operating in the first atmospheric window 2007 ,		1
2	Room-temperature short-wavelength ($\lambda = 3.7\mu\text{m}$) GaInAs/AlAsSb quantum-cascade lasers. <i>Applied Physics Letters</i> , 2006 , 88, 121127	3.4	35
1	Above room-temperature GaInAs/Al(Ga)AsSb quantum cascade lasers. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2006 , 3, 415-418		